



GP
ELECTRONICS

RB751M3-40

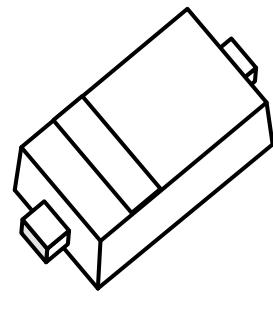
40V-30mA Schottky Barrier Diode

RB751M3-40 Schottky Barrier Diode

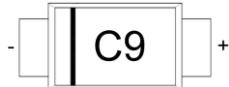
Feature

- Low Forward Voltage
- Low IR
- High Reliability

SOD-323F



MARKING:



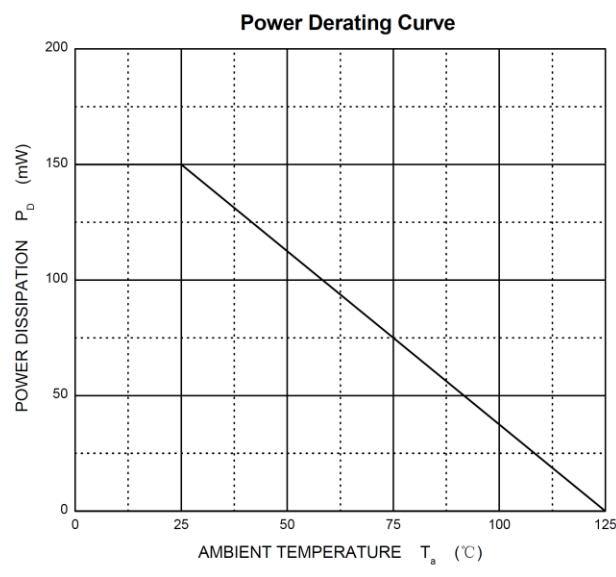
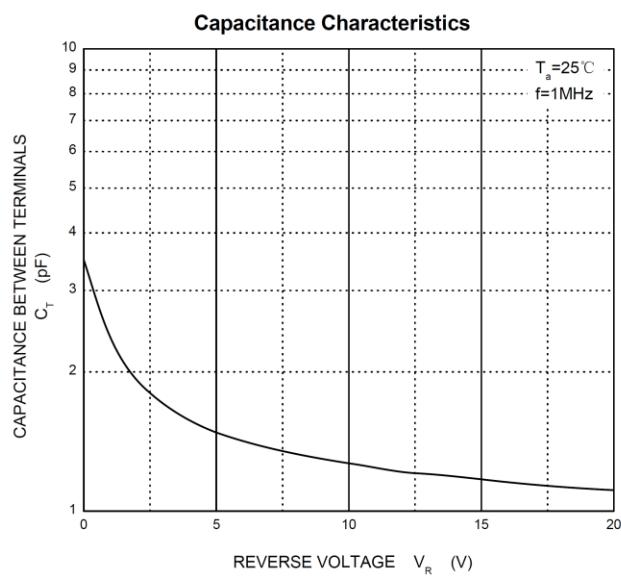
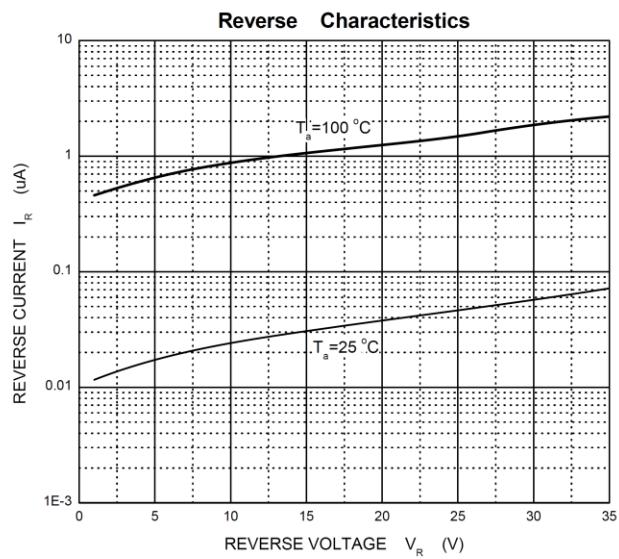
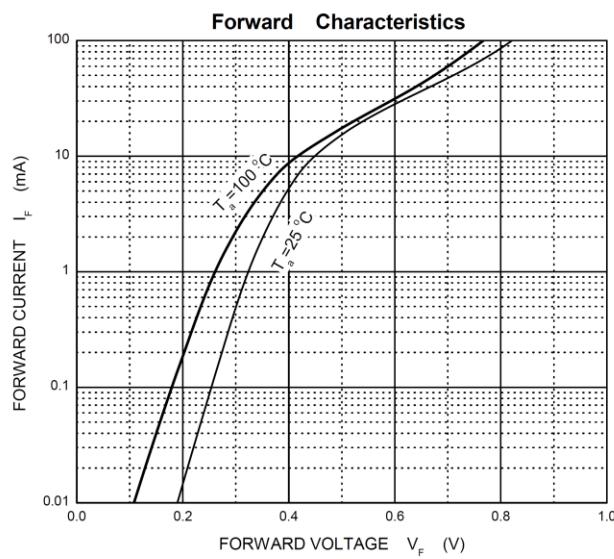
ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

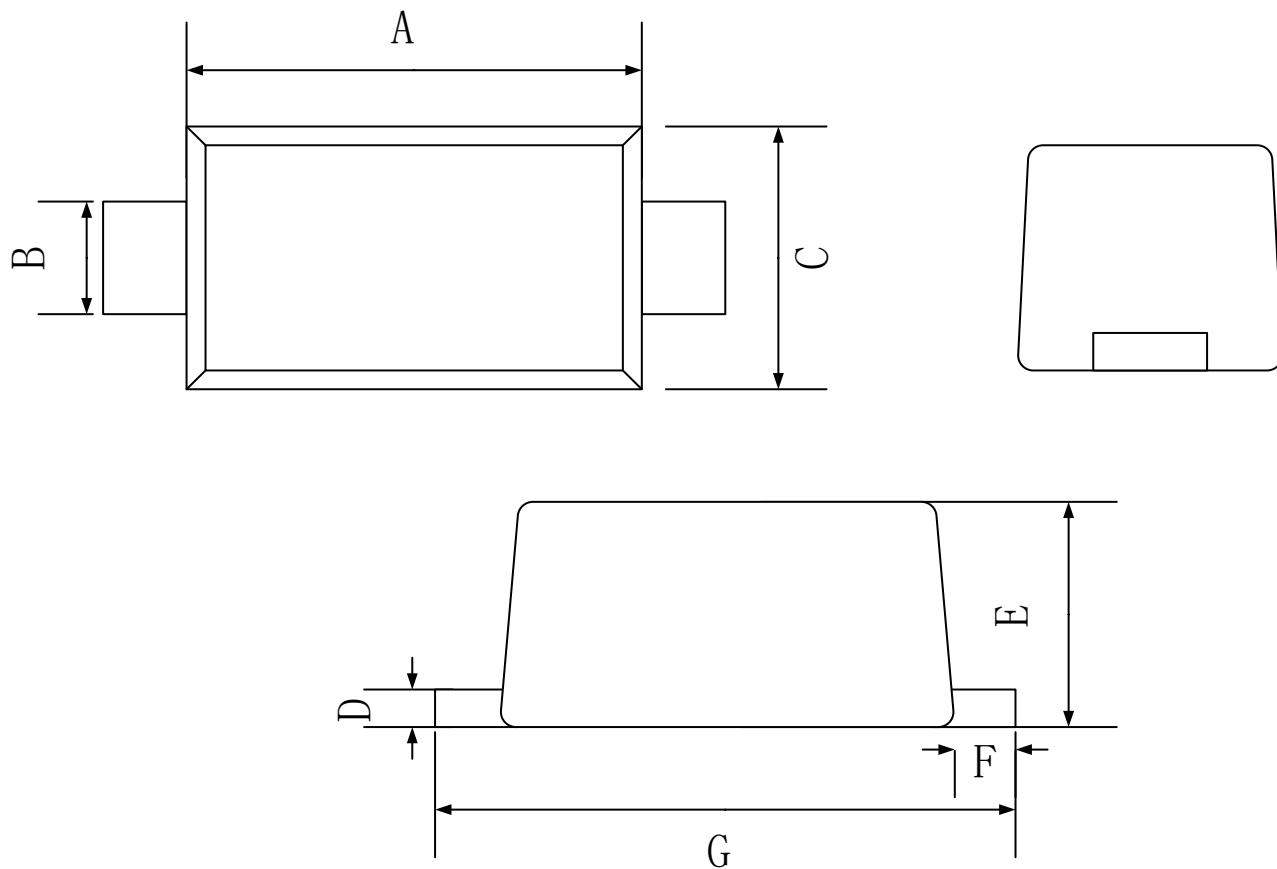
Parameter	Symbol	Value	Unit
DC reverse voltage	V_R	40	V
Mean rectifying current	I_O	30	mA
Non-repetitive Peak Forward Surge Current @ $t=8.3\text{ms}$	I_{FSM}	200	mA
Power Dissipation	P_D	0.15	W
Junction Temperature	T_J	125	$^\circ\text{C}$
Storage Temperature Range	T_{STG}	-55 ~ +150	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Reverse voltage	V_{BR}	$I_R = 100\mu\text{A}$	40			V
Forward voltage	V_F	$I_F = 1\text{mA}$			0.37	V
Reverse current	I_R	$V_R = 30\text{V}$			0.5	μA
Capacitance between terminals	C_T	$VR=1\text{V}, f=1\text{MHz}$		2		pF

Typical Characteristics



SOD-323F Package Outline Dimensions


Symbol	Dimensions In Millimeters		
	Min.	Typ.	Max.
A	1.60	1.70	1.80
B	0.25	0.38	0.45
C	1.15	0.25	1.35
D	0.06	0.10	0.21
E	0.60	0.65	0.75
F	0.40 REF		
G	2.30	2.50	2.70